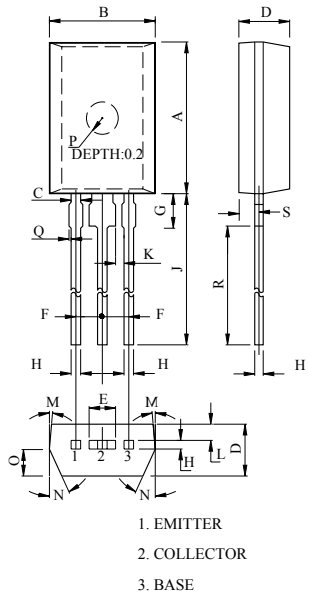
KTC3467

EPITAXIAL PLANAR NPN TRANSISTOR

HIGH-DEFINITION CRT DISPLAY
VIDEO OUTPUT APPLICATION.

FEATURES

- High Voltage : V_{CEO}=200V.
- High Transition Frequency : f_T=150MHz(Typ.).
- Low Collector Output Capacitance : C_{ob}=1.7pF(Typ.).
- Complementary to KTA1070.



DIM	MILLIMETERS
A	7.20 MAX
B	5.20 MAX
C	0.60 MAX
D	2.50 MAX
E	1.15 MAX
F	1.27
G	1.70 MAX
H	0.55 MAX
J	14.00±0.50
K	0.35 MIN
L	0.75±0.10
M	4°
N	25°
O	1.25
P	Φ1.50
Q	0.10 MAX
R	12.50±0.50
S	1.00

TO-92L

MAXIMUM RATING (Ta=25℃)

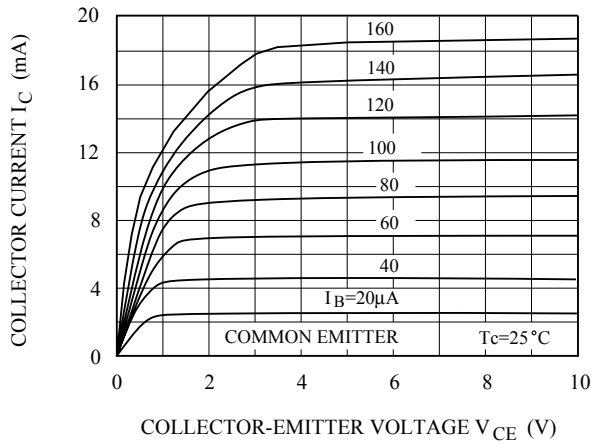
CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	200	V
Collector-Emitter Voltage		V_{CEO}	200	V
Emitter-Base Voltage		V_{EBO}	5	V
Collector Current	DC	I_C	100	mA
	Pulse	I_{cp}	200	
Collector Power Dissipation		P_C	1	W
Junction Temperature		T_j	150	℃
Storage Temperature Range		T_{stg}	-55～150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃)

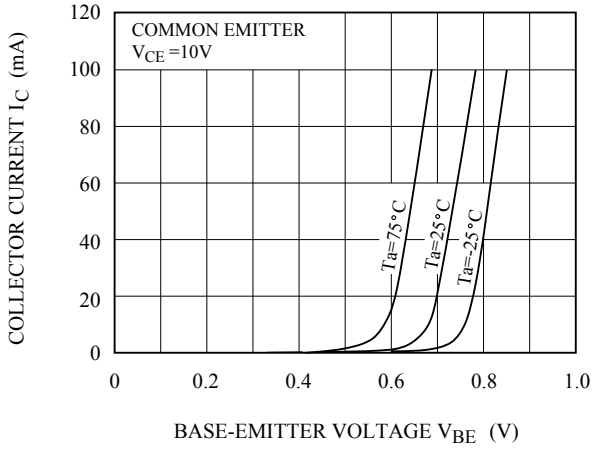
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB}=150V, I_E=0	-	-	0.1	μA
Emitter Cut-off Current	I_{EBO}	V_{EB}=4V, I_C=0	-	-	0.1	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=1mA, I_B=0	200	-	-	V
DC Current Gain	h_{FE}	V_{CE}=5V, I_C=10mA	70	-	240	-
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=20mA, I_B=2mA	-	-	0.6	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=20mA, I_B=2mA	-	-	1.0	V
Transition Frequency	f_T	V_{CE}=30V, I_C=10mA	-	150	-	MHz
Collector Output Capacitance	C_{ob}	V_{CB}=30V, I_E=0, f=1MHz	-	1.7	-	pF
Reverse Transfer Capacitance	C_{re}	V_{CB}=30V, I_E=0, f=1MHz	-	1.2	-	pF

Note : h_{FE} Classification 0:70～140 , Y:120～240

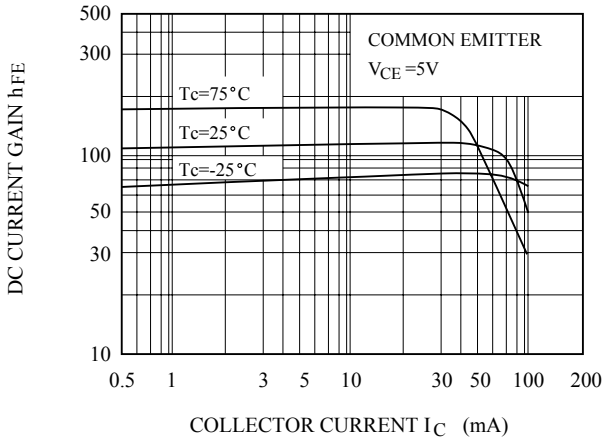
I_C - V_{CE}



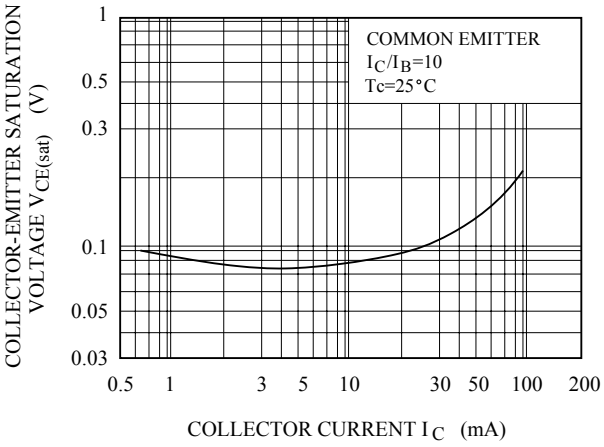
I_C - V_{BE}



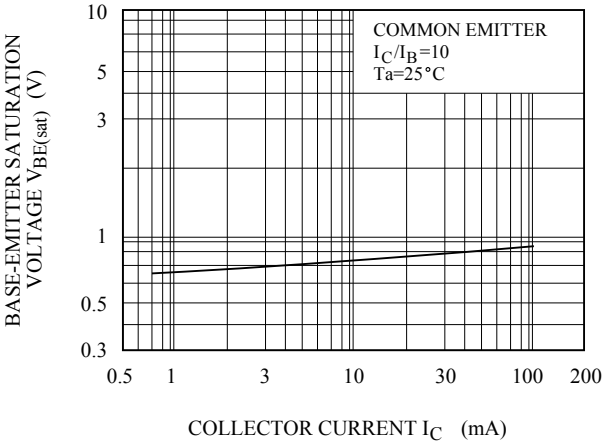
h_{FE} - I_C



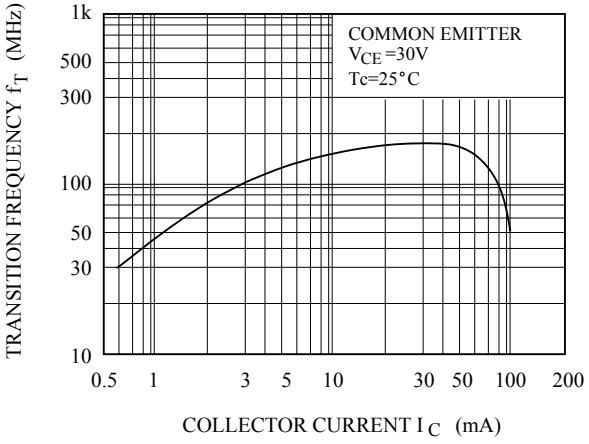
$V_{CE(sat)}$ - I_C



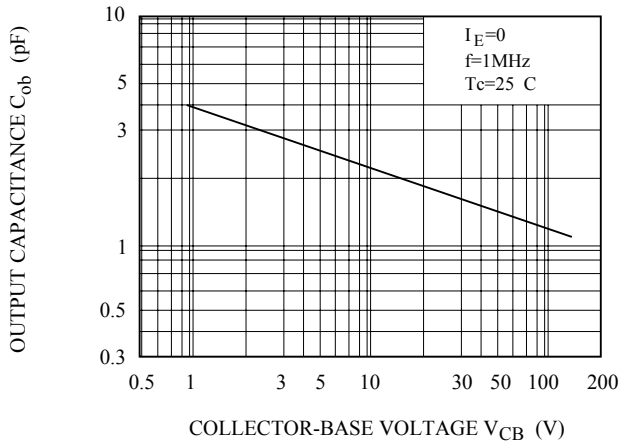
$V_{BE(sat)}$ - I_C



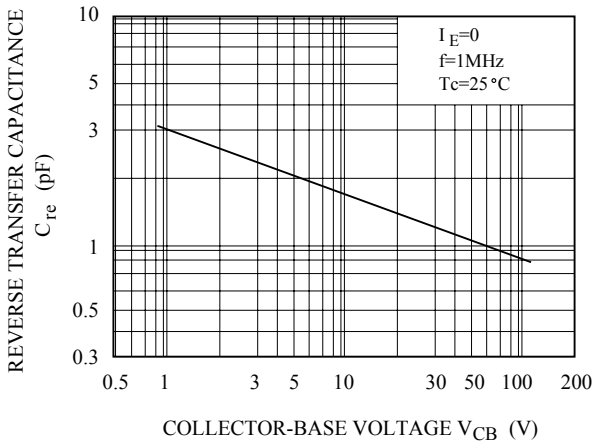
f_T - I_C



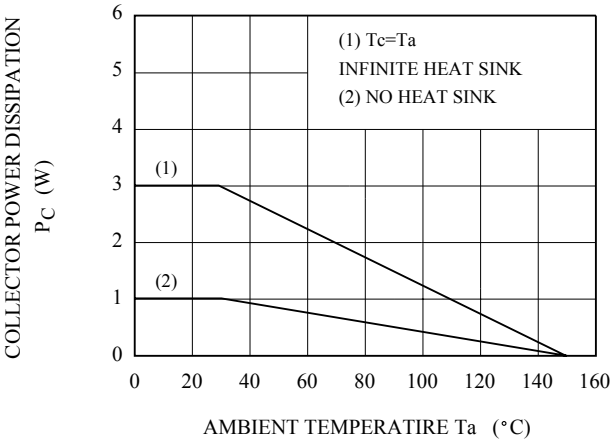
C_{ob} - V_{CB}



C_{re} - V_{CB}



Pc - Ta



SAFE OPERATING AREA